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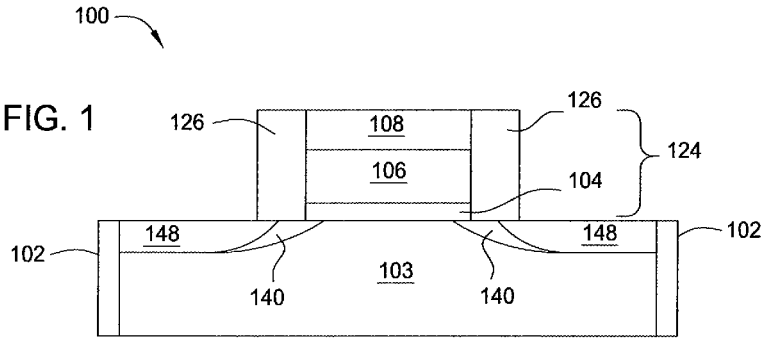
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(54) Title: BORON NITRIDE AND BORON-NITRIDE DERIVED MATERIALS DEPOSITION METHOD

FIG. 1



(57) Abstract: A method and apparatus are provided to form spacer materials adjacent substrate structures. In one embodiment, a method is provided for processing a substrate including placing a substrate having a substrate structure adjacent a substrate surface in a deposition chamber, depositing a spacer layer on the substrate structure and substrate surface, and etching the spacer layer to expose the substrate structure and a portion of the substrate surface, wherein the spacer layer is disposed adjacent the substrate structure. The spacer layer may comprise a boron nitride material. The spacer layer may comprise a base spacer layer and a liner layer, and the spacer layer may be etched in a two-step etching process.

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